PRELIMINARY PRODUCT INFORMATION



MOS INTEGRATED CIRCUIT $\mu PD78F0701Y$

8-BIT SINGLE-CHIP MICROCONTROLLER

The μ PD78F0701Y is a μ PD780701Y sub-series product of the 78K/0 series. The μ PD78F0701Y features a DCAN controller and an IEBus to controller. It also features flash memory as internal ROM. Programs can be written into the flash memory without having to remove it from the board.

The functions of the μ PD78F0701Y are described in the following user's manuals. Be sure to read these manuals when designing a system based on the μ PD78F0701Y.

μPD780701Y Sub-Series User's Manual : U13781E 78K/0 Series User's Manual, Instruction : U12326E

FEATURES

- Built-in IEBus (Inter Equipment BusTM) controller
- Built-in DCAN (Direct Storage Controller Area Network) controller
- Pin-compatible with masked ROM versions (other than the VPP pin)
- Flash memory : 60K bytes (supported for self-programming)
- Internal high-speed RAM: 1,024 bytes
 Internal expansion RAM: 2,048 bytes
- ★ Buffer RAM for DCAN : 288 bytes
- ★ Can be operated within the same power supply voltage ranges as masked ROM versions (VDD = 3.5 to 5.5 V)

Remark For differences between flash memory versions and masked ROM versions, see Chapter 1.

APPLICATIONS

Car audio systems, etc.

ORDERING INFORMATION

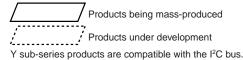
Part number	Package
μPD78F0701YGC-8BT	80-pin plastic QFP (14 × 14 mm)

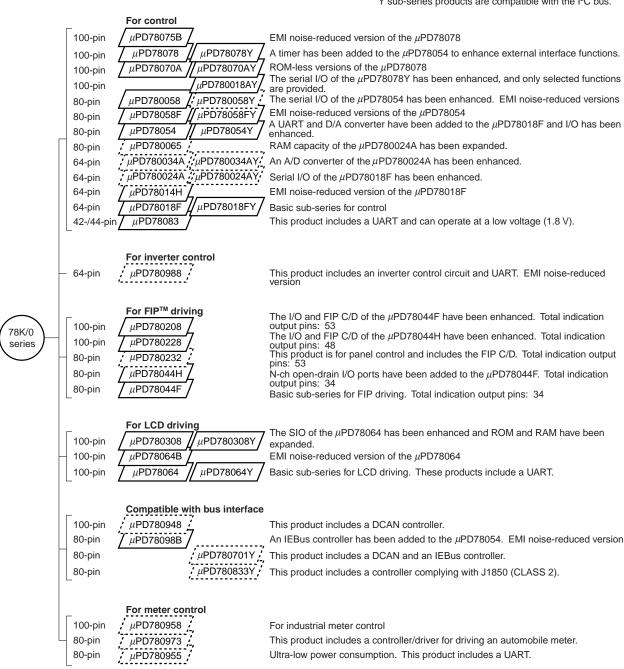
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

The information contained in this document is being issued in advance of the production cycle for the device. The parameters for the device may change before final production or NEC Corporation, at its own discretion, may withdraw the device prior to its production.

★ 78K/0 SERIES DEVELOPMENT

The 78K/0 series products are shown below. The sub-series names are indicated in frames.







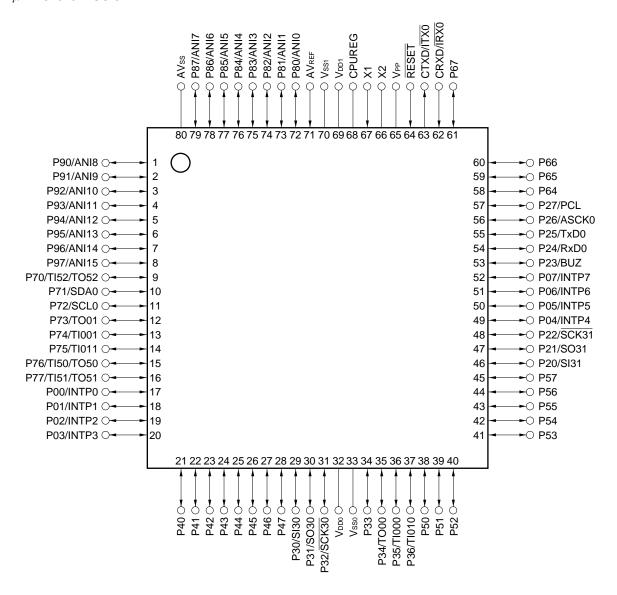
FUNCTIONS

	Item	Function			
Internal memory	Flash memory	60K bytes			
	High-speed RAM	1,024 bytes			
	Extended RAM	2,048 bytes			
	Buffer RAM for DCAN	288 bytes			
Minimum instructi	on execution time	On-chip minimum instruction execution time modification function • $0.32~\mu\text{s}/0.64~\mu\text{s}/1.27~\mu\text{s}/2.54~\mu\text{s}/5.09~\mu\text{s}$ (operation with system clock running at 6.29 MHz)			
General-purpose	registers	8 bits \times 32 registers (8 bits \times 8 registers \times 4 banks)			
Instruction set		 16-bit operations Multiplication/division (8 bits × 8 bits, 16 bits ÷ 8 bits) Bit manipulations (such as set, reset, test, and Boolean operation) 			
I/O ports		Total : 67 CMOS I/O : 56 TTL input/CMOS output : 8 N-ch open-drain I/O : 3			
A/D converters		16 channels with 8-bit resolutionPower failure detection function			
Serial interface		Three-wire serial I/O mode: 2 channels UART mode: 1 channel I'C bus mode: 1 channel			
Timers		16-bit timer/event counters: 2 channels 8-bit timer/event counters: 3 channels Watch timer: 1 channel Watchdog timer: 1 channel			
Timer output		5 lines (8-bit PWM output: 3 lines)			
DCAN controller		1 channel			
IEBus controller		Effective transmission rate: 18 kbps			
Clock output		49.2 kHz, 98.3 kHz, 197 kHz, 393 kHz, 786 kHz, 1.57 MHz, 3.15 MHz, 6.29 MHz (operation with system clock running at 6.29 MHz)			
Buzzer output		0.768 kHz, 1.54 kHz, 3.07 kHz, 6.14 kHz (operation with system clock running at 6.29 MHz)			
Vectored	Maskable	Internal: 20, External: 8			
interrupt	Nonmaskable	Internal: 1			
sources	Software	1			
Power supply volt	age	V _{DD} = 3.5 to 5.5 V			
Operating ambien	t temperature	T _A = -40°C to +85°C			
Package		80-pin plastic QFP (14 × 14 mm)			

*

PIN CONFIGURATION (TOP VIEW)

• 80-pin plastic QFP (14 \times 14 mm) μ PD78F0701YGC-8BT



Cautions 1. In normal operation mode, connect the VPP pin directly to the Vsso or Vss1 pin.

- 2. Connect the AVss pin to the Vsso pin.
- 3. Connect the AVREF pin to the VDD0 pin.



ANI0-ANI15 : Analog Input P90-P97 : Port 9

ASCKO : Asynchronous Serial Clock PCL : Programmable Clock

AVREF : Analog Reference Voltage RESET : Reset

AVss : Analog Ground : Receive Data (for UART0)

BUZ : Buzzer Output : SCK30, SCK31 : Serial Clock (for SIO30, SIO31)

CPUREG : Regulator for CPU Power Supply SCL0 : Serial Clock (for IIC0)

CRXD : CAN Receive Data SDA0 : Serial Data
CTXD : CAN Transmit Data SI30, SI31 : Serial Input
INTP0-INTP7 : Interrupt from Peripherals SO30, SO31 : Serial Output

IRX0: IEBus Receive DataTI000, TI010, TI001,ITX0: IEBus Transmit DataTI011, TI50, TI51,

P00-P07 : Port 0 Tl52 : Timer Input

P20-P27 : Port 2 TO00, TO01, TO50,

P30-P36 : Port 3 TO51, TO52 : Timer Output

P40-P47 : Port 4 TxD0 : Transmit Data (for UART0)

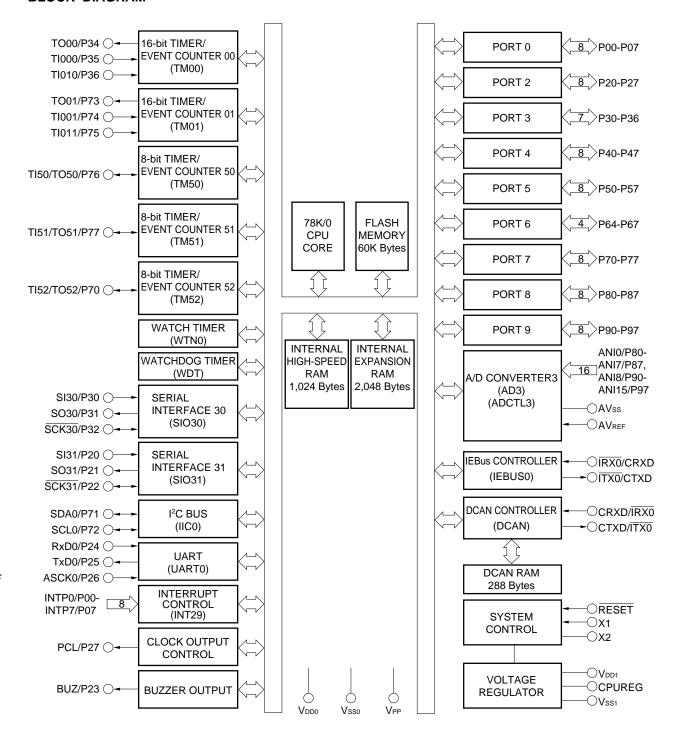
P50-P57 : Port 5 VDD0, VDD1 : Power Supply

P64-P67 : Port 6 VPP : Programming Power Supply

P70-P77 : Port 7 V_{SS0}, V_{SS1} : Ground P80-P87 : Port 8 X1, X2 : Crystal



BLOCK DIAGRAM





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1. DIFFERENCES BETWEEN THE μ PD78F0701Y AND MASKED ROM VERSIONS

The μ PD78F0701Y is a product provided with flash memory that enables writing, erasing, and rewriting of programs without being removed from the board.

Table 1-1 shows the differences between the flash memory version (μ PD78F0701Y) and masked ROM versions (μ PD780701Y and μ PD780702Y).

Table 1-1. Differences between the μ PD78F0701Y and Masked ROM Versions

Item		μPD78F0701Y	μPD780701Y	μPD780702Y
Internal ROM	l type	Flash memory	Masked ROM	
IC pin		Not provided	Provided	
V _{PP} pin		Provided	Not provided	
Built-in bus c	ontroller	DCAN controller and IEBus controller	DCAN controller	IEBus controller
TX pin		DCAN or IEBus output (switched by software)	DCAN output	IEBus output
RX pin		DCAN or IEBus input (switched by software) DCAN input IEBus input		IEBus input
Electrical cha	aracteristics	Refer to the data sheet of individual products.		

Caution The flash memory versions and masked ROM versions have different noise immunity and noise radiation characteristics. Do not use ES products for evaluation when considering switching from flash memory versions to those using masked ROM upon the transition from preproduction to mass-production. CS products (masked ROM versions) should be used in this case.

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2. PIN FUNCTIONS

2.1 Port Pins (1/2)

	Pin name	I/O	F	unction	When reset	Also used as
*	P00-P07	I/O	Port 0 8-bit input/output port Can be set to either input o Whether an on-chip pull-up specified by software.	Input	INTP0-INTP7	
	P20	I/O	Port 2		Input	SI31
	P21		8-bit input/output port	an analysis for A. I. M. and Ma		SO31
	P22		Can be set to either input o Whether an on-chip pull-up	resistor is to be used can be		SCK31
*	P23		specified by software.			BUZ
	P24					RxD0
	P25					TxD0
	P26					ASCK0
	P27					PCL
*	P30	I/O	Port 3	Whether an on-chip pull-up	Input	SI30
	P31		7-bit input/output port Can be set to either input	resistor is to be used can be specified by software.		SO30
	P32		or output in 1-bit units.	specified by software.		SCK30
	P33			N-ch open-drain input/output port (15-V withstand voltage) Can directly drive LEDs.		-
*	P34			Whether an on-chip pull-up		TO00
	P35			resistor is to be used can be		T1000
	P36			specified by software.		TI010
*	P40-P47	I/O	specified by software.	r output in 1-bit units. resistor is to be used can be cted, the interrupt request flag	Input	-
*	P50-P57	I/O	Port 5 8-bit input/output port TTL-level input and CMOS Can be set to either input o Whether an on-chip pull-up specified by software.	Input	-	
*	P64-P67	I/O	Port 6 4-bit input/output port Can be set to either input o Whether an on-chip pull-up specified by software.	r output in 1-bit units. resistor is to be used can be	Input	-



2.1 Port Pins (2/2)

Pin name I/O Function When reset Also used as Port 7 Whether an on-chip pull-up I/O P70 Input TI52/TO52 8-bit input/output port resistor is to be used can be Can be set to either input specified by software. or output in 1-bit units. N-ch open-drain input/output P71 SDA0 port (5-V withstand voltage) P72 SCL0 P73 Whether an on-chip pull-up TO01 resistor is to be used can be P74 TI001 specified by software. P75 TI011 P76 TI50/TO50 P77 TI51/TO51 I/O P80-P87 Port 8 Input ANI0-ANI7 8-bit input/output port Can be set to either input or output in 1-bit units. P90-P97 I/O ANI8-ANI15 Input 8-bit input/output port Can be set to either input or output in 1-bit units.

2.2 Non-Port Pins (1/2)

Pin name	I/O	Function	When reset	Also used as
INTP0-INTP7	Input	External interrupt input for which effective edges (rising and/or falling edges) can be specified.	Input	P00-P07
SI30	Input	Serial data input to serial interface	Input	P30
SI31				P20
SO30	Output	Serial data output to serial interface	Input	P31
SO31				P21
SDA0	I/O	Serial data input/output to serial interface	Input	P71
SCK30	I/O	Serial clock input/output to serial interface	Input	P32
SCK31				P22
SCL0				P72
RxD0	Input	Serial data input to asynchronous serial interface	Input	P24
TxD0	Output	Serial data output to asynchronous serial interface	Input	P25
ASCK0	Input	Serial clock input to asynchronous serial interface	Input	P26
CRXD	Input	DCAN controller (DCAN) data input	Input	ĪRX0
CTXD	Output	DCAN controller (DCAN) data output	Output	ĪTX0
ĪRX0	Input	IEBus controller (IEBUS0) data input	Input	CRXD
ĪTX0	Output	IEBus controller (IEBUS0) data output	Output	CTXD

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2.2 Non-Port Pins (2/2)

Pin name	I/O	Function	When reset	Also used as
TI000	Input	External count clock input to 16-bit timer (TM00)	Input	P35
TI010		External count clock input to 16-bit timer (TM00)		P36
TI001		External count clock input to 16-bit timer (TM01)		P74
TI011		External count clock input to 16-bit timer (TM01)		P75
TI50		External count clock input to 8-bit timer (TM50)		P76/TO50
TI51		External count clock input to 8-bit timer (TM51)		P77/TO51
TI52		External count clock input to 8-bit timer (TM52)		P70/TO52
TO00	Output	16-bit timer (TM00) output	Input	P34
TO01		16-bit timer (TM01) output		P73
TO50		8-bit timer (TM50) output		P76/TI50
TO51		8-bit timer (TM51) output		P77/TI51
TO52		8-bit timer (TM52) output		P70/TI52
PCL	Output	Clock output	Input	P27
BUZ	Output	Buzzer output	Input	P23
ANI0-ANI7	Input	A/D converter (AD3) analog input	Input	P80-P87
ANI8-ANI15				P90-P97
AVREF	Input	A/D converter (AD3) reference voltage and analog power supply	-	-
AVss	-	A/D converter (AD3) ground potential	-	-
X1	Input	Connected to crystal for system clock oscillation	-	-
X2	-		-	-
RESET	Input	System reset input	Input	-
CPUREG	-	CPU supply voltage regulator. Connect this pin to the Vsso or Vss1 pin through a 0.1-µF capacitor.	-	-
V _{DD0}	-	Positive supply voltage for ports	-	-
V _{DD1}	-	Positive supply voltage (except ports and analog section)	-	-
Vsso	-	Ground potential for ports	_	-
Vss1	_	Ground potential (except ports and analog section)	-	-
Vpp	-	This pin applies a high voltage when a program is written or verified. In normal operation mode, connect this pin directly to the Vsso or Vss1 pin.	-	-



2.3 Pin Input/Output Circuits and Handling of Unused Pins

Table 2-1 lists the types of input/output circuits for each pin and explains how unused pins are handled.

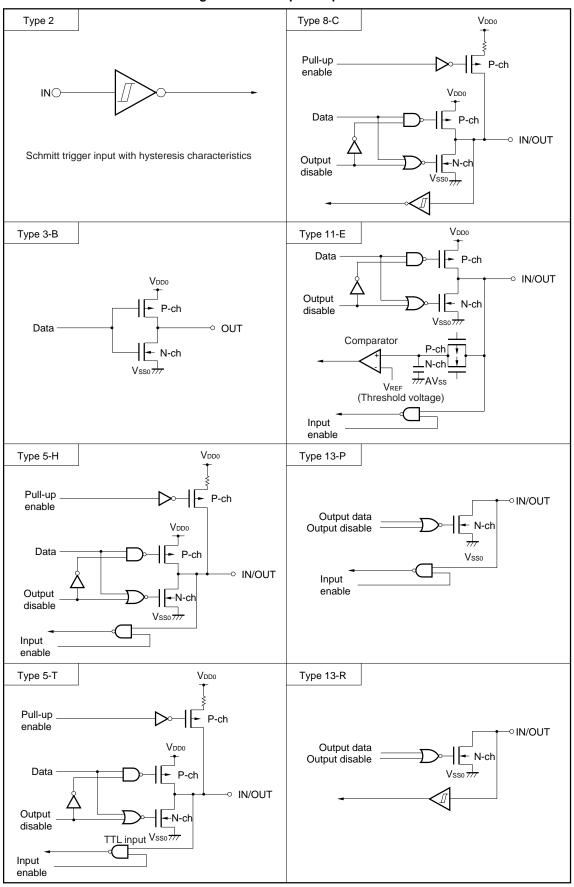
Figure 2-1 shows the configuration of each type of input/output circuit.

Table 2-1. Types of Input/Output Circuit for Each Pin and Handling of Unused Pins

Pin name	I/O circuit type	I/O	Recommended connection of unused pins	
P00/INTP0-P07/INTP7	8-C	I/O	Connect these pins to the Vsso pin via respective resistors.	
P20/SI31			Connect these pins to the V _{DD0} or V _{SS0} pin via respective	
P21/SO31	5-H		resistors.	
P22/SCK31	8-C			
P23/BUZ	5-H			
P24/RxD0	8-C			
P25/TxD0	5-H			
P26/ASCK0	8-C			
P27/PCL	5-H			
P30/SI30	8-C			
P31/SO30	5-H			
P32/SCK30	8-C			
P33	13-P		Connect this pin to the VDDO pin via resistors.	
P34/TO00	5-H		Connect these pins to the VDDO or VSSO pin via respective	
P35/TI000	8-C		resistors.	
P36/TI010				
P40-P47	5-H		Connect these pins to the VDDD pin via respective resistors.	
P50-P57	5-T		Connect these pins to the VDDO or VSSO pin via respective	
P64-P67	5-H		resistors.	
P70/TI52/TO52				
P71/SDA0	13-R		Connect these pins to the VDDD pin via respective resistors.	
P72/SCL0				
P73/TO01	5-H		Connect these pins to the VDDO or VSSO pin via respective	
P74/TI001	8-C		resistors.	
P75/TI011				
P76/TI50/TO50				
P77/TI51/TO51				
P80/ANI0-P87/ANI7	11-E			
P90/ANI8-P97/ANI15				
CRXD/IRX0	2	Input	Connect this pin to the VDDO or VSSO pin via resistors.	
CTXD/ITX0	3-B	Output	Leave this pin open.	
RESET	2	Input	-	
AVREF	-		Connect this pin to the VDD0 pin.	
AVss		-	Connect this pin to the Vsso pin.	
VPP			Connect this pin directly to the Vsso or Vss1 pin.	



Figure 2-1. Pin Input/Output Circuits



* 3. SELECTING INTERNAL BUS CONTROLLERS (DCAN and IEBus)

The μ PD78F0701Y has two internal bus controllers: a DCAN controller and IEBus controller. These bus controllers cannot be used simultaneously.

By default, the DCAN controller is selected.

The IEBus controller is selected by making the IEBus unit active (by setting bit 7 (ENIEBUS) of the IEBus control register 0 (BRC0) to 1).

The default statuses of the interrupt request signals and pins differ depending on which of the internal bus controllers is used.

Table 3-1 shows the default statuses of the interrupt request signals and pins.

Table 3-1. Default Statuses of Interrupt Request Signals and Pins

Item	Using DCAN controller	Using IEBus controller	
Default status of CTXD/ITX0 pin	High level	Low level	
Interrupt request signals	INTCR	INTIE1	
	INTCT	INTIE2	
	INTCE	None	

Note The statuses of the flags corresponding to the interrupt signals also differ.



★ 4. MEMORY SIZE SELECT REGISTER (IMS)

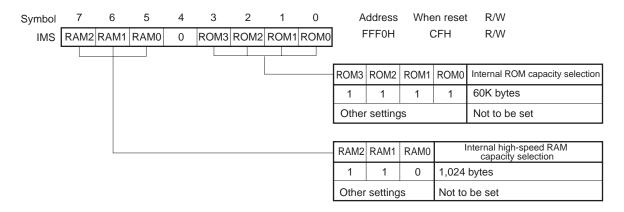
The memory size select register (IMS) selects the internal memory size.

This register is set by an 8-bit memory manipulation instruction.

RESET input sets IMS to CFH.

Caution Use IMS with its default value (CFH). Do not set any other values for the IMS.

Figure 4-1. Format of Memory Size Select Register (IMS)



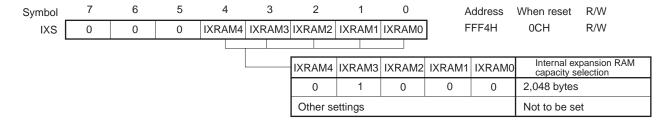
★ 5. INTERNAL EXPANSION RAM SIZE SELECT REGISTER (IXS)

The internal expansion RAM size select register (IXS) selects the internal expansion RAM capacity. This register is set by a 1-bit or 8-bit memory manipulation instruction.

RESET input sets IXS to 0CH.

Caution Set IXS to 08H as the default status of the program. Because IXS is set to 0CH at a reset, set it to 08H after a reset.

Figure 5-1. Format of Internal Expansion RAM Size Select Register (IXS)



***** 6. FLASH MEMORY PROGRAMMING

The flash memory can be written even while the device is mounted on the target system (on-board write). To write a program into the flash memory, connect the dedicated flash writer (Flashpro III (model number: FL-PR3 and PG-FP3)) to both the host machine and target system.

A program can also be written by using an adapter, for flash memory writing, connected to the Flashpro III.

Remark The FL-PR3 is manufactured by Naito Densei Machida Mfg. Co., Ltd.

6.1 Selecting the Transmission Method

The Flashpro III writes into flash memory by means of serial transmission. The transmission method to be used for writing is selected from those listed in Table 6-1. To select a transmission method, use the format shown in Figure 6-1, according to the number of VPP pulses listed in Table 6-1.

Transmission method	Number of channels	Pins	Number of VPP pulses		
Three-wire serial I/O	2	SI30/P30 SO30/P31 SCK30/P32	0		
		SI31/P20 SO31/P21 SCK31/P22	1		
l ² C bus	1	SDA0/P71 SCL0/P72	4		
UART	1	RxD0/P24 TxD0/P25	8		

Table 6-1. Transmission Methods

Caution To select a transmission method, always use the corresponding number of VPP pulses listed in Table 6-1.

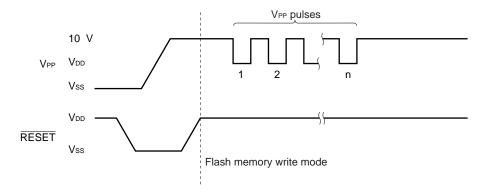


Figure 6-1. Format of Transmission Method Selection



6.2 Flash Memory Programming Functions

Flash memory writing and other operations can be performed by transmitting/receiving commands and data according to the selected transmission method. Table 6-2 lists the main flash memory programming functions.

Table 6-2. Main Flash Memory Programming Functions

Function	Description
Reset	Stops writing or detects communication synchronization.
Batch verify	Compares the entire contents of memory with the input data.
Batch internal verify	Compares the entire contents of memory in different modes.
Batch erase	Erases the entire contents of memory.
Batch blank check	Checks that the entire contents of memory have been erased.
High-speed write	Writes to the flash memory according to the specified write start address and number of data bytes to be written.
Continuous write	Continues writing based on the information input by using the high-speed write function.
Batch prewrite	Writes 00H into the entire contents of memory.
Status	Checks the current operation mode and whether the operation has terminated.
Oscillation frequency setting	Inputs the frequency information of the resonator.
Erase time setting	Inputs the memory erase time.
Baud rate setting	Sets the communication rate in UART mode.
I ² C communication mode setting	Sets standard or high-speed mode upon communication via I ² C.
Silicon signature read	Outputs the device name, memory capacity, and device block information.

6.3 Connecting the Flashpro III

The connection between the Flashpro III and μ PD78F0701Y varies with the transmission method. Figures 6-2 to 6-4 show the connection for each transmission method.

Figure 6-2. Flashpro III Connection in Three-Wire Serial I/O Mode

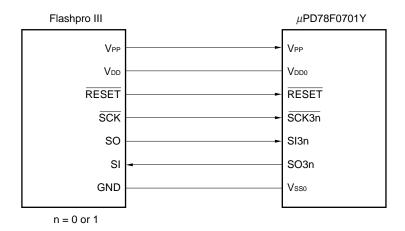


Figure 6-3. Flashpro III Connection in I²C Bus Mode

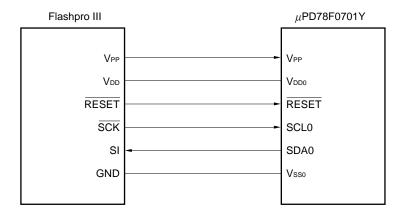
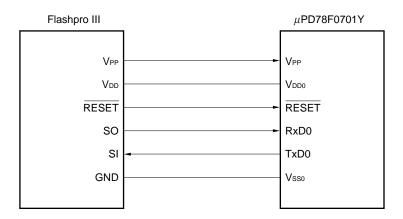


Figure 6-4. Flashpro III Connection in UART Mode



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★ 6.4 Flash Memory Programming by Self-Writing

The flash memory of the μ PD78F0701Y can be rewritten by a program.

(1) Configuration of flash memory

0000H

Figure 6-5 shows the configuration of the flash memory.

Normal operation mode Self-writing mode Erase/write routine call Internal extension Internal extension RAM are (2K bytes) RAM are (2K bytes) F000H F000H **EFFFH EFFFH** 9BFFH FLPMC - 09H Firmware area Flash memory area (erase/write routine (60K bytes) Erase/write included) Flash memory area Cannot be (60K bytes) 8000H accessed by an FLPMC - 08H ordinary instruction.

0000H

Figure 6-5. Configuration of Flash Memory

(2) Flash programming mode control register (FLPMC)

The flash programming mode control register (FLPMC) is used to select an operation mode and check the status of the VPP pin.

This register is set with a 1-bit or 8-bit memory manipulation instruction.

RESET input sets FLPMC to 08H.

Figure 6-6. Format of Flash Programming Mode Control Register (FLPMC)

Symbol	7	6	5	4	3	2	1	0	Address	When reset	R/W
FLPMC	0	0	0	0	1	VPP	0	FLSPM0	FFCDH	08H ^{Note 1}	R/W ^{Note 2}
	VPP		P	Applied vo	Itage of V						
	0		The voltage necessary for erasing/writing flash memory is not applied to the V_PP pin.								
	1	A voltage higher than that on the $V_{\text{\tiny DD}}$ pin is applied to the $V_{\text{\tiny PP}}$ pin									

FLSPM0	Operation mode selection						
0	0 Normal operation mode						
1	Self-writing mode						

Notes 1. Bit 2 changes depending on the level of the VPP pin.

2. Bit 2 is a read-only bit.

Cautions 1. Clear bits 1 and 4 to 7 to 0, and set bit 3 to 1.

2. The VPP bit indicates the status of the voltage applied to the VPP pin. When the VPP bit is "0", the voltage necessary for erasing/writing the flash memory is not applied to the VPP pin. However, the voltage necessary for erasing/writing is not always applied even when the VPP bit is "1". Configure the hardware so that the necessary voltage is accurately applied to the VPP pin. To check whether the necessary voltage is also applied to the VPP pin by software, not only by hardware, use an external hardware detection circuit and its output signals.



(3) Self writing procedure

The procedure for self writing the flash memory is as follows (see Figure 6-7):

- (1) Disable the interrupts.
- (2) Set self-writing mode (FLPMC = 09H).
- (3) Select register bank 3.
- (4) Specify the first address of the entry RAM to the HL register.
- (5) VPP: ON (ON signal for power IC).
- (6) Check the VPP level.
- (7) Initialize the flash subroutine.
- (8) Set the parameters.
- (9) Control the flash memory (erasing, writing, etc.).
- (10) VPP: OFF (OFF signal for power IC).
- (11) Normal operation mode (FLPMC = 08H)

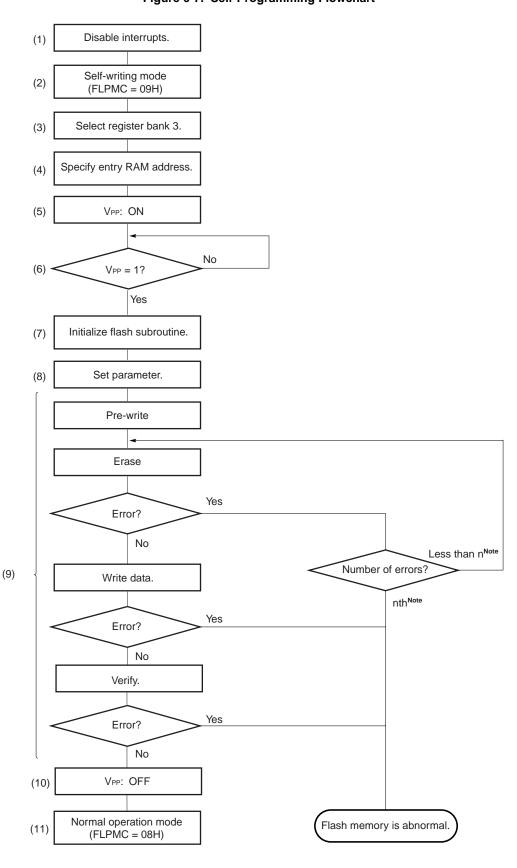
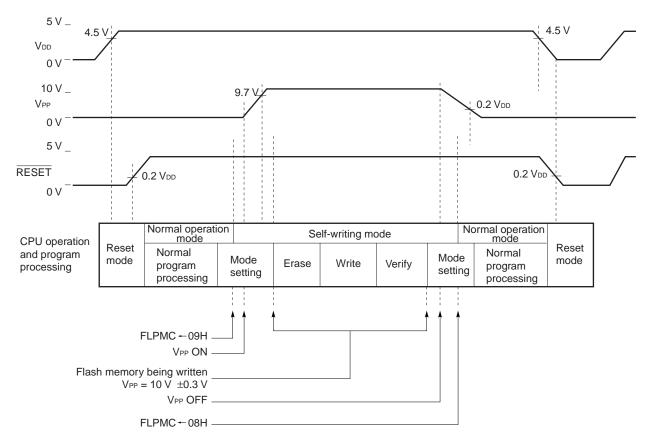


Figure 6-7. Self-Programming Flowchart

Note This differs depending on the user program.









(4) CPU resources

The CPU resources used for self-writing the flash memory are as follows:

Register bank: BANK3 (8 bytes)

B register: Status flag

C register: Function number

HL register: Entry RAM area first address

Stack area: 16 bytes MAX.
Write data storage area: 1 to 256 bytes
Entry RAM area: 32 bytes

RAM area used by self-writing subroutine. Can be specified by user by using HL register.

Status flag

7	6	5	4	3	2	1	0
Parameter setting error	-	-	Verify error	Write error	-	Blank check error	-

(5) Entry RAM area

Table 6-3 shows the contents of the entry RAM area.

Table 6-3. Entry RAM Area

Offset value	Contents
+0	Reserved area (1 byte)
+1	Reserved area (1 byte)
+2	Flash memory start address (2 bytes)
+4	Flash memory end address (2 bytes)
+6	Number of bytes written to flash memory (1 byte)
+7	Write time data (1 byte)
+8	Erase time data (3 bytes)
+11	Reserved area (3 bytes)
+14	Write data storage buffer first address (2 bytes)
+16	Total number of blocks (1 byte)
+17	Total number of areas (1 byte)
+18	Reserved area (14 bytes)
:	

Example: When the value of the HL register in register bank 3 is 0FD00H

0FD00H: Status

0FD02H: Flash memory start address

0FD06H: Number of bytes written to flash memory

:

The following explains the entry RAM area in detail.

(a) Flash memory start address

Flash memory address value used for _FlashByteWrite subroutine

(b) Flash memory end address

Flash memory address value used for _FlashGetInfo subroutine

(c) Number of bytes written to flash memory

Area number and number of bytes written to flash memory

(d) Write time

Set one of the following values according to the operating frequency.

fx (MHz)	Set value
1.00 to 1.28	20H
1.29 to 2.56	40H
2.57 to 5.12	60H
5.13 to 8.38	80H

(e) Erase time data

Set value = Erase time (s) × Operating frequency/29 + 1

(Erase time range: 0.5 to 20 s)

Example: When the erase time is two seconds and the operating frequency is 6.29 MHz

Set value = 2 × 6,291,456/512 + 1 = 24,577 (decimal) = 6001H (hexadecimal)

(f) Write data storage buffer first address

This area stores the first address of the write data storage buffer area. The data (write data) in the RAM addressed by using the data in this area is written into flash memory (_FlashByteWrite subroutine). Up to 256 bytes of write data can be specified with the data in this area as the first address.

(g) Total number of blocks

Total number of flash memory blocks stored by _FlashGetInfo subroutine

(h) Total number of areas

Total number of flash memory areas stored by _FlashGetInfo subroutine



(6) Self-writing subroutine

Table 6-4 lists the subroutines to be used for self-writing and their functions.

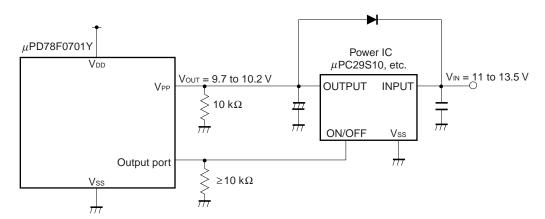
Table 6-4. Self-Writing Subroutines

Function No.		Subroutine name	Function
Decimal	Hexa- decimal		
0	00H	_FlashEnv	Initializes flash subroutine.
1	01H	_FlashSetEnv	Sets parameter.
2	02H	_FlashGetInfo	Reads flash memory information.
16	10H	_FlashAreaBlankCheck	Blank check of specified area
32	20H	_FlashAreaPreWrit	Pre-write of specified area
48	30H	_FlashAreaErase	Erases specified area
80	50H	_FlashByteWrite	Successive write in byte units
96	60H	_FlashArealVerify	Internal verification of specified area

(7) Configuration of self-writing circuit

Figure 6-9 shows the configuration of the self-writing circuit.

Figure 6-9. Configuration of Self-Writing Circuit





7. ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Parameter	Symbol	Conditi	ions		Rated value	Unit
Supply voltage	VDD VDD = AVREF			-0.3 to +6.5	V	
	AVREF					
	VPP				-0.3 to +10.5	V
	AVss				-0.3 to +0.3	V
Input voltage	VII	P50-P57, P64-P67, P70-P7	P00-P07, P20-P27, P30-P32, P34-P36, P40-P47, P50-P57, P64-P67, P70-P77, P80-P87, P90-P97, CRXD/ĪRXO, X1, X2, RESET			V
	V _{I2}	P33	N-ch ope	n drain	-0.3 to +16	V
Output voltage	Vo	P00-P07, P20-P27, P30-P3 P64-P67, P70-P77, P80-P8	•		-0.3 to V _{DD} + 0.3	V
Analog input voltage	Van	P80-P87, P90-P97	Analog ir	put pin	AVss - 0.3 to AVREF + 0.3 and -0.3 to Vdd + 0.3	V
High-level output current	Іон	P00-P07, P20-P27, P30-P32, P34-P36, P40-P47, P50-P57, P64-P67, P70, P73-P77, P80-P87, P90-P97, CTXD/ITX0 per pin		-10	mA	
		Total for all pins			-30	mA
Low-level output current	Note IOL	P00-P07, P20-P27, P30-P3. P36, P40-P47, P50-P57, P6	•	Peak value	20	mA
		P70-P77, P80-P87, P90-P9 CTXD/ITX0 per pin	7,	rms value	10	mA
		P33		Peak value	30	mA
				rms value	15	mA
		Total for all pins		Peak value	100	mA
				rms value	60	mA
Operating ambient temperature	TA				-40 to +85	°C
Programming ambient temperature					-10 to +55	°C
Storage temperature	T _{stg}	Before 2,000 hours elapses programming was performed		memory	-65 to +150	°C
		After flash memory program and 2,000 hours or more ha	•	performed	-65 to +125	°C

Note To obtain the rms value, calculate [rms value] = [peak value] $\times \sqrt{\text{duty}}$.

Caution Absolute maximum ratings are rated values beyond which physical damage will be caused to the product; if the rated value of any of the parameters in the above table is exceeded, even momentarily, the quality of the product may deteriorate. Always use the product within its rated values.

Remark Unless otherwise specified, the characteristics of a dual-function pin are the same as those of the corresponding port pin.

CHARACTERISTICS OF THE SYSTEM CLOCK OSCILLATION CIRCUIT (TA = -40°C to +85°C, VDD = 3.5 to 5.5 V)

Resonator	Recommended circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Crystal	V _{PP} X2 X1 R1 \(\frac{1}{2} \)	Oscillation frequency (fx) Note 1			6.29 Note 2		MHz
	C2 C1 C1	Oscillation settling Note 3 time				30	ms

Notes 1. Only the characteristics of the oscillation circuit are indicated.

- **2.** 6.29 = 6.291456 (MHz)
- **3.** Time required for oscillation to settle once a reset sequence ends or STOP mode is deselected.

Caution When using the system clock oscillation circuit, observe the following conditions for the wiring of that section enclosed in dotted lines in the above diagrams, so as to avoid the influence of the wiring capacitance.

- . Keep the wiring as short as possible.
- Do not allow signal wires to cross one another.
- Keep the wiring away from wires that carry a high, non-stable current.
- Keep the grounding point of the capacitors at the same level as Vss1.
- Do not connect the grounding point to a grounding wire that carries a high current.
- Do not extract a signal from the oscillation circuit.



DC CHARACTERISTICS (TA = -40°C to +85°C, VDD = 3.5 to 5.5 V)

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
High-level input voltage	VIH1	P21, P23, P25, P64-P67, P73, I		31, P34, P40-P47, 7, P90-P97	0.7V _{DD}		VDD	V
	V _{IH2}			24, P26, P30, P32, P35, 7, CRXD/ĪRX0, RESET	0.8V _{DD}		V _{DD}	V
	V _{IH3}	P50-P57			2.3		V _{DD}	V
	V _{IH4}	P33		N-ch open drain	0.7V _{DD}		15	V
	V _{IH5}	X1, X2			V _{DD} - 0.5		V _{DD}	V
Low-level input voltage	VIL1	P21, P23, P25, P64-P67, P73, I		31, P34, P40-P47, 7, P90-P97	0		0.3V _{DD}	٧
	VIL2			24, P26, P30, P32, P35, 7, CRXD/IRX0, RESET	0		0.2Vdd	>
	V _{IL3}	P50-P57			0		0.75	٧
	VIL4	P33		N-ch open drain	0		0.3V _{DD}	٧
	V _{IL5}	X1, X2			0		0.4	٧
High-level output voltage	Vон1	Iон = -1 mA	P00-P07, P20-P27, P30-P32, P34-P36, P40-P47, P50-P57, P64-P67, P70, P73-P77, P80-P87, P90-P97, CTXD/ITX0		V _{DD} - 1.0		V _{DD}	>
	V _{OH2}	Іон = -100 μΑ			V _{DD} - 0.5		V _{DD}	V
Low-level output voltage	V _{OL1}	IoL = 15 mA	P33			0.4	2.0	V
	VOL2	IoL = 1.6 mA	P71,	P72			0.4	V
	Vol3	IoL = 1 mA		07, P20-P27, P30-P32, 36, P40-P47, P50-P57,			1.0	V
	Vol4	Ιοι = 100 μΑ		67, P70, P73-P77, 87, P90-P97, CTXD/ ITX0			0.5	V
High-level input leakage current	Іин1	Vin = Vdd	P34-P P64-P	07, P20-P27, P30-P32, 36, P40-P47, P50-P57, 67, P70-P77, P80-P87, 97, CRXD/ĪRX0, RESET			3	μΑ
	ILIH2		X1, X	2			20	μΑ
	Іпнз	VIN = 15 V	P33				80	μΑ
Low-level input leakage current	Iul1	Vin = 0 V	P34-P P64-P	07, P20-P27, P30-P32, 36, P40-P47, P50-P57, 67, P70-P77, P80-P87, 97, CRXD/IRX0, RESET			-3	μΑ
	ILIL2		X1, X	2			-20	μΑ
	Ішз		,	during other than input ction execution)			-3	μΑ

Note During input instruction execution, a leakage current of -200 μ A (MAX.) is input to P33 for one clock (during no wait).

Remark Unless otherwise specified, the characteristics of a dual-function pin are the same as those of the corresponding port pin.



DC CHARACTERISTICS (TA = -40°C to +85°C, VDD = 3.5 to 5.5 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
High-level output leakage current	Ісон	Vout = Vdd	P00-P07, P20-P27, P30-P36, P40-P47, P50-P57, P64-P67, P70-P77, P80-P87, P90-P97, CTXD/ITX0			3	μΑ
Low-level output leakage current	ILOL	Vout = 0 V	P00-P07, P20-P27, P30-P36, P40-P47, P50-P57, P64-P67, P70-P77, P80-P87, P90-P97, CTXD/ITX0			-3	μΑ
Software pull-up resistor	R ₁	V _{IN} = 0 V	P00-P07, P20-P27, P30-P32, P34-P36, P40-P47, P50-P57, P64-P67, P70, P73-P77	15	30	90	kΩ
Power supply current Note 1	I _{DD1}	6.29-MHz crysta	6.29-MHz crystal oscillation operating mode		4.0	20	mA
	I _{DD2}	6.29-MHz crysta	6.29-MHz crystal oscillation HALT mode Note 2		500	1,000	μΑ
	IDD3	STOP mode			0.1	30	μΑ

- **Notes 1.** The current flowing through the V_{DD1} pin. The power supply current does not include the current flowing through the A/D converter and on-chip pull-up resistors.
 - **2.** During low-speed mode operation (when 04H is loaded into the processor clock control register (PCC)). The power supply current does not include the current for peripheral circuit operation.

Remark Unless otherwise specified, the characteristics of a dual-function pin are the same as those of the corresponding port pin.



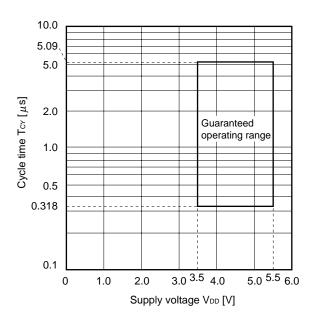
AC CHARACTERISTICS

(1) Basic operations (T_A = -40°C to +85°C, V_{DD} = 3.5 to 5.5 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Cycle time (minimum instruction execution time)	Тсч	System clock operation (at fx = 6.291456 MHz)	0.318		5.09	μs
TI000, TI010, TI001, and TI011 input high/low level width	t тiно t тilo		4/f _{sam} + Note 0.25			μs
TI50, TI51, and TI52 input frequency	fтı5				2	MHz
TI50, TI51, and TI52 input high/low level width	t тін5 t тіL5		200			ns
Interrupt request input high/low level width	tinth tintl	INTP0 to INTP7, P40 to P47	10			μs
RESET low level width	trsl		10			μs

Note $f_x/2$, $f_x/4$, or $f_x/64$ can be selected as f_{sam} by using bits 0 and 1 (PRM0n0 and PRM0n1) of the prescaler mode register 0n (PRM0n). If the valid edge of Tl00n is selected as the count clock, however, $f_{sam} = f_x/8$ (n = 0 or 1).

Tcy vs VDD (with system clock running)





(2) Serial interface ($T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{DD} = 3.5$ to 5.5 V)

(a) Three-wire serial I/O mode (SCK30...Internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK30 cycle time	tkcy1		1.9			μs
SCK30 high/low level width	tkH1 tkL1		tkcy1/2 - 50			ns
SI30 setup time (for SCK30 ↑)	tsıĸı		100			ns
SI30 hold time (for SCK30 ↑)	tksı1		400			ns
Delay from SCK30 ↓ to SO30 output	tkso1	C = 100 pF ^{Note}			300	ns

Note C is the capacitance of the $\overline{SCK30}$ and SO30 output line.

(b) Three-wire serial I/O mode (SCK30...External clock input)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK30 cycle time	tkCY2		800			ns
SCK30 high/low level width	tкн2 tкL2		400			ns
SI30 setup time (for SCK30 ↑)	tsık2		100			ns
SI30 hold time (for SCK30 ↑)	tksi2		400			ns
Delay from SCK30 ↓ to SO30 output	tks02	C = 100 pF ^{Note}			300	ns

Note C is the capacitance of the SO30 output line.



(c) Three-wire serial I/O mode (SCK31...Internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK31 cycle time	tксүз		1.9			μs
SCK31 high/low level width	tкнз tкLз		tксу1/2 - 50			ns
SI31 setup time (for SCK31 ↑)	tsıкз		100			ns
SI31 hold time (for SCK31 ↑)	t ksi3		400			ns
Delay from SCK31 ↓ to SO31 output	tks03	C = 100 pF ^{Note}			300	ns

Note C is the capacitance of the $\overline{\text{SCK31}}$ and SO31 output line.

(d) Three-wire serial I/O mode (SCK31...External clock input)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK31 cycle time	tkcy4		800			ns
SCK31 high/low level width	tkH4 tkL4		400			ns
SI31 setup time (for SCK31 ↑)	tsık4		100			ns
SI31 hold time (for SCK31 ↑)	Tksi4		400			ns
Delay from SCK31 ↓ to SO31 output	tkso4	C = 100 pF ^{Note}			300	ns

Note C is the capacitance of the SO31 output line.



(e) UART mode (dedicated baud rate generator output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					38,836	bps

(f) UART mode (external clock input)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
ASCK0 cycle time	tксүз		800			ns
ASCK0 high/low level width	t кнз, t кLз		400			ns
Transfer rate					39,063	bps

(g) I2C bus mode

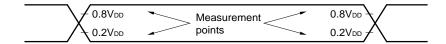
Parameter		Symbol	Symbol Standard mode		High-spe	Unit	
			MIN.	MAX.	MIN.	MAX.	
SCL0 clock frequency		fscL	0	100	0	400	kHz
Bus free time (between stop-start conditions)		tBUF	4.7	-	1.3	-	μs
Note 1 Hold time		thd:STA	4.0	-	0.6	-	μs
SCL0 clock	c low level width	tLOW	4.7	-	1.3	-	μs
SCL0 clock	k high level width	tніgн	4.0	-	0.6	-	μs
Start/resta	Start/restart condition setup time		4.7	-	0.6	1	μs
Data	CBUS-compatible master	thd:dat	5.0	-	=	1	μs
hold time	I ² C bus		Note 2	-	0 Note 2	0.9 Note 3	μs
Data setup	Data setup time		250	-	100 Note 4	-	ns
SDA0 and	SDA0 and SCL0 signal rising time		-	1,000	-	300	ns
SDA0 and SCL0 signal falling time		t⊧	-	300	-	300	ns
Stop condition setup time		tsu:sto	4.0	-	0.6	-	μs
Pulse width of spikes controlled by the input filter		tsp	-	-	0	50	ns
Capacitive load of each bus line		Cb	-	400	-	400	pF

Notes 1. In the start condition, the first clock pulse is generated after this period of time.

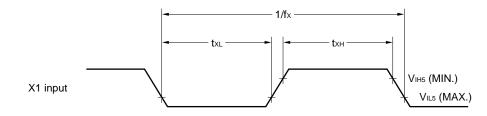
- 2. To fill the undefined area of the SCL0 falling edge (at V_{IHmin.} of the SCL0 signal), the device needs to internally provide a hold time of at least 300 ns for the SDA0 signal.
- 3. If the device does not extend the low hold time (tLow) of the SCL0 signal, the maximum data hold time (thd:dat) only needs to be satisfied.
- **4.** High-speed mode I²C bus can be used in standard mode I²C bus system. In this case, the following conditions must be satisfied:
 - When the device does not extend the low hold time of the SCL0 signal $tsu:DAT \ge 250 \text{ ns}$
 - When the device extends the low hold time of the SCL0 signal
 Before SCL0 is released (tRmax. + tsu:DAT = 1,000 + 250 = 1,250 ns: for standard mode I²C bus system), the next data bit must be sent onto the SDA0 line.



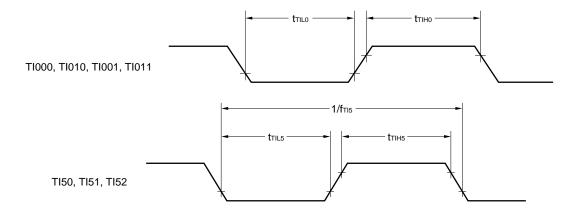
AC TIMING MEASUREMENT POINTS (except the X1 inputs)



CLOCK TIMING



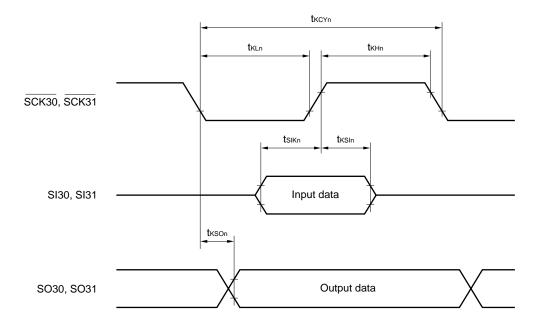
TI TIMING





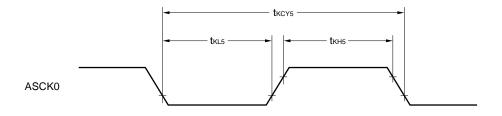
SERIAL TRANSFER TIMING

Three-Wire Serial I/O Mode:

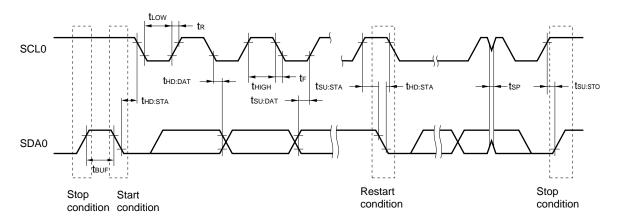


n = 1-4

UART Mode (External Clock Input):



I²C Bus Mode:





IEBUS 0 CONTROLLER CHARACTERISTICS (TA = -40°C to +85°C, VDD = 3.5 to 5.5 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
IEBus system clock frequency	fs	Fixed to mode 1		6.29		MHz
Driver delay (from ITX0 output to bus line)	tотх	$C = 50 \text{ pF}^{\text{Note}}$ The μ PC2590 is used as a driver/receiver.			1.5	μs
Receiver delay (from bus line to IRX0 input)	torx	The μ PC2590 is used as a driver/receiver.			0.7	μs
Transmission delay on bus	tobus	The μ PC2590 is used as a driver/receiver.			0.85	μs

Note C is the load capacitance of the $\overline{\text{ITX0}}$ output line.

Remarks 1. Although the IEBus standard recommends the 6.0-MHz system clock frequency, the μ PD78F0701Y guarantees normal operation of the IEBus controller at 6.29 MHz.

2. fs: System clock frequency of the IEBus controller

A/D CONVERTER CHARACTERISTICS (Ta = -40°C to +85°C, VDD = AVREF = 3.5 to 5.5 V, Vss = AVss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution			8	8	8	bit
Total error					±0.6	%
Conversion time	tconv		14		100	μs
Analog input voltage	VIAN		AVss		AVREF	V
AVREF resistance	Rairef		T.B.D	28	T.B.D	kΩ

Note No quantization error ($\pm 0.2\%$) is included. This parameter is indicated as the ratio to the full-scale value.

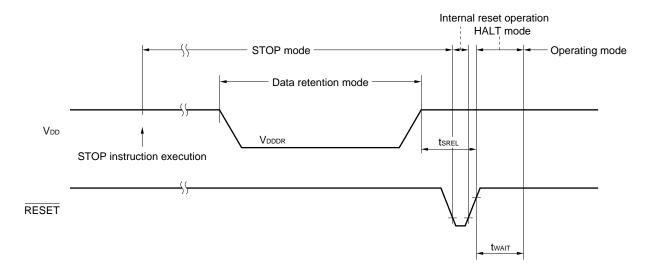


DATA MEMORY STOP MODE LOW SUPPLY VOLTAGE DATA RETENTION CHARACTERISTICS ($T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$)

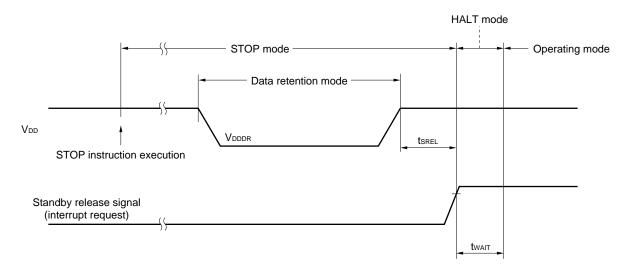
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		2.0		5.5	V
Data retention supply current	IDDDR	V _{DDDR} = 2.0 V		0.1	10	μΑ
Release signal set time	t srel		0			μs
Oscillation settling time	twait	Released by RESET		2 ¹⁷ /fx		ms
		Released by interrupt		Note		ms

Note Selection of $2^{12}/fx$, $2^{14}/fx$, $2^{19}/fx$, or $2^{21}/fx$ is available by bits 0 to 2 (OSTS0 to OSTS2) of the oscillation settling time selection register (OSTS).

DATA RETENTION TIMING (STOP mode release by RESET)

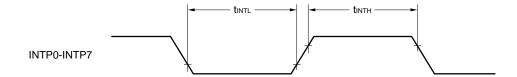


DATA RETENTION TIMING (standby release signal: STOP mode release by interrupt signal)

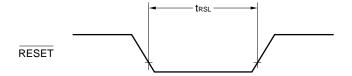




INTERRUPT REQUEST INPUT TIMING

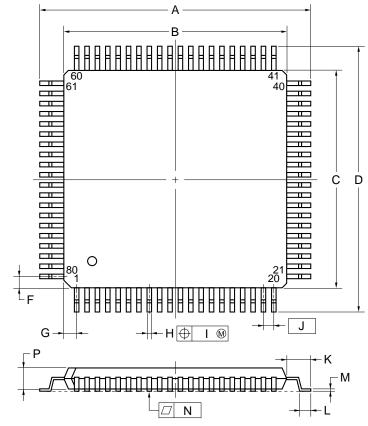


RESET INPUT TIMING

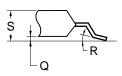


8. PACKAGE DRAWINGS

80 PIN PLASTIC QFP (14×14)



detail of lead end



NOTE

Each lead centerline is located within 0.13 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
Α	17.20±0.20	0.677±0.008
В	14.00±0.20	$0.551\substack{+0.009 \\ -0.008}$
С	14.00±0.20	$0.551^{+0.009}_{-0.008}$
D	17.20±0.20	0.677±0.008
F	0.825	0.032
G	0.825	0.032
Н	0.32±0.06	0.013+0.002
I	0.13	0.005
J	0.65 (T.P.)	0.026 (T.P.)
K	1.60±0.20	0.063±0.008
L	0.80±0.20	$0.031^{+0.009}_{-0.008}$
М	0.17+0.03	0.007+0.001
N	0.10	0.004
Р	1.40±0.10	0.055±0.004
Q	0.125±0.075	0.005±0.003
R	3°+7°	3°+7°
S	1.70 MAX.	0.067 MAX.

P80GC-65-8BT



APPENDIX A DEVELOPMENT TOOLS

The following development tools are available for developing systems using the μ PD78F0701Y. Be sure to see notes described in **(5)**.

(1) Language processing software

RA78K/0	Assembler package used in common with the 78K/0 series	
CC78K/0	compiler package used in common with the 78K/0 series	
DF780701 ^{Note}	Device file for the μPD780701Y sub-series	
CC78K/0-L	C compiler library source file used in common with the 78K/0 series	

Note Under development

(2) Flash memory write tools

*	Flashpro III (model No. FL-PR3, PG-FP3)	Flash writer used only for microcontrollers with internal flash memory
	FA-80GC	Flash memory write adapter. Connect this adapter to the Flashpro III. This adapter is dedicated to the 80-pin plastic QFP (GC-8BT type).
*	Floashpro III controller	Program controlled by a personal computer and which is supported by Flashpro III. Runs under Windows 95, etc.

(3) Debugging tools

• When in-circuit emulator IE-78K0-NS is used

IE-78K0-NS	In-circuit emulator used in common with the 78K/0 series
IE-70000-MC-PS-B	Power supply unit for the IE-78K0-NS
IE-70000-98-IF-C	Interface adapter required when a PC-9800 series computer (other than a notebook type) is used as the host machine (C bus supported)
IE-70000-CD-IF-A	PC card and interface cable required when a notebook-type computer is used as the host machine (PCMCIA socket supported)
IE-70000-PC-IF-C	Interface adapter required when an IBM PC/AT or compatible is used as the host machine (ISA bus supported)
IE-70000-PCI-IF	Interface adapter when using PC that incorporates PCI bus as host machine
IE-780701-NS-EM1 Note	Emulation board used to emulate the μ PD780701Y sub-series products
NP-80GC	Emulation probe dedicated to the 80-pin plastic QFP (GC-8BT type)
EV-9200GC-80	Conversion socket for connecting the target system board created for the 80-pin plastic QFP (GC-8BT type) with the NP-80GC
ID78K0-NS	Integrated debugger for IE-78K0-NS
SM78K0	System simulator used in common with the 78K/0 series
DF780701 Note	Device file for the μ PD780701Y sub-series

Note Under development

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• When in-circuit emulator IE-78001-R-A is used

IE-78001-R-A	In-circuit emulator used in common with the 78K/0 series
IE-70000-98-IF-C	Interface adapter required when a PC-9800 series computer (other than a notebook type) is used as the host machine (C bus supported)
IE-70000-PC-IF-C	Interface adapter required when an IBM PC/AT or compatible is used as the host machine (ISA bus supported)
IE-70000-PCI-IF	Interface adapter when using PC that incorporates PCI bus as host machine
IE-78000-R-SV3	Interface adapter and cable required when an EWS is used as the host machine
IE-780701-NS-EM1 Note	Emulation board used to emulate the μ PD780701Y sub-series
IE-78K0-R-EX1	Emulation probe conversion board required when the IE-780701-NS-EM1 is used with the IE-78001-R-A
EP-78230GC-R	Emulation probe dedicated to the 80-pin plastic QFP (GC-8BT type)
EV-9200GC-80	Conversion socket for connecting the target system board created for the 80-pin plastic QFP (GC-8BT type) with the EP-78230GC-R
ID78K0	Integrated debugger for IE-78001-R-A
SM78K0	System simulator used in common with the 78K/0 series
DF780701 Note	Device file for the μ PD780701Y sub-series

Note Under development

(4) Real-time OS

RX78K/0	Real-time OS for the 78K/0 series
MX78K0	OS for the 78K/0 series

(5) Notes on using development tools

- ID78K0-NS, ID78K0, and SM78K0 are to be used in combination with DF780701.
- CC78K/0 and RX78K/0 are to be used in combination with RA78K/0 and DF780701.
- FL-PR3, FA-80GC, and NP-80GC are manufactured by Naito Densei Machida Mfg. Co., Ltd. (044-822-3813). Contact NEC sales representatives for purchase.
- For third party development tools, refer to the 78K/0 Series Selection Guide (U11126E).
- The host machines and OSs supporting each software product are as follows:

Host machine [OS]	PC	EWS
Software	PC-9800 series [Windows] IBM PC/AT and compatibles [Japanese/English Windows]	HP9000 series 700 TM [HP-UX TM] SPARCstation TM [SunOS TM , Solaris TM] NEWS TM (RISC) [NEWS-OS TM]
RA78K/0	O ^{Note}	О
CC78K/0	O ^{Note}	О
ID78K0-NS	0	-
ID78K0	O	O
SM78K0	O	-
RX78K/0	O ^{Note}	О
MX78K0	O ^{Note}	0

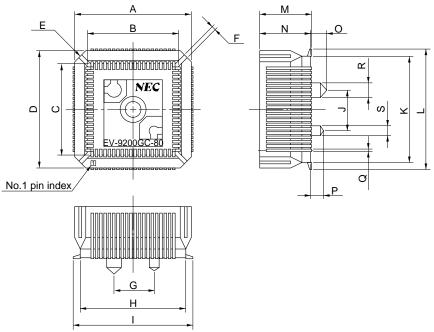
Note DOS-based software



PACKAGE DRAWINGS OF THE CONVERSION SOCKET (EV-9200GC-80) AND RECOMMENDED PATTERN ON BOARDS

Figure A-1. Package Drawings of the EV-9200GC-80 (Reference)

Based on EV-9200GC-80 (1) Package drawing (in mm)

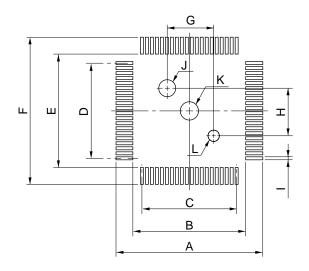


EV-9200GC-80-G0E

ITEM	MILLIMETERS	INCHES
Α	18.0	0.709
В	14.4	0.567
С	14.4	0.567
D	18.0	0.709
Е	4-C 2.0	4-C 0.079
F	0.8	0.031
G	6.0	0.236
Н	16.0	0.63
1	18.7	0.736
J	6.0	0.236
K	16.0	0.63
L	18.7	0.736
М	8.2	0.323
0	8.0	0.315
N	2.5	0.098
Р	2.0	0.079
Q	0.35	0.014
R	φ2.3	φ0.091
S	1.5	0.059

Figure A-2. Recommended Pattern for Mounting the EV-9200GC-80 on Boards (Reference)

Based on EV-9200GC-80 (2) Pad drawing (in mm)



EV-9200GC-80-P1E

ITEM	MILLIMETERS	INCHES
Α	19.7	0.776
В	15.0	0.591
С	0.65±0.02 × 19=12.35±0.05	$0.026^{+0.001}_{-0.002} \times 0.748 = 0.486^{+0.003}_{-0.002}$
D	0.65±0.02 × 19=12.35±0.05	$0.026^{+0.001}_{-0.002}$ $0.748=0.486^{+0.003}_{-0.002}$
Е	15.0	0.591
F	19.7	0.776
G	6.0±0.05	$0.236^{+0.003}_{-0.002}$
Н	6.0±0.05	$0.236^{+0.003}_{-0.002}$
I	0.35±0.02	$0.014^{+0.001}_{-0.001}$
J	φ2.36±0.03	ϕ 0.093 ^{+0.001} _{-0.002}
K	φ2.3	φ0.091
L	φ1.57±0.03	ϕ 0.062 ^{+0.001} _{-0.002}

Caution Dimensions of mount pad for EV-9200 and that for target device (QFP) may be different in some parts. For the recommended mount pad dimensions for QFP, refer to "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (C10535E).



APPENDIX B RELATED DOCUMENTS

• Documents related to devices

Document name	Document No.	
	Japanese	English
μPD780701Y Sub-Series User's Manual	U13781J	U13781E
μ PD780701Y, 780702Y Preliminary Product Information	U13920J	U13920E
μ PD78F0701Y Preliminary Product Information	U13563J	This manual
78K/0 Series User's Manual, Instruction	U12326J	U12326E

• Documents related to development tools (user's manual)

Document name		Document No.	
		Japanese	English
RA78K0 Assembler Package	Operation	U11802J	U11802E
	Language	U11801J	U11801E
	Structured Assembly Language	U11789J	U11789E
RA78K Series Structured Assembler Preprocessor		U12323J	EEU-1402
CC78K0 C Compiler	Operation	U11517J	U11517E
	Language	U11518J	U11518E
CC78K/0 C Compiler Application Note	Programming Know-How	U13034J	U13034E
IE-78K0-NS		To be created	To be created
IE-78001-R-A		To be created	To be created
IE-78K0-R-EX1		To be created	To be created
IE-780701-NS-EM1		To be created	To be created
EP-78230		EEU-985	EEU-1515
SM78K0 System Simulator Windows Base	Reference	U10181J	U10181E
SM78K Series System Simulator	External Parts User Open Interface Specifications	U10092J	U10092E
ID78K0-NS Integrated Debugger Windows Base	Reference	U12900J	U12900E
ID78K0 Integrated Debugger EWS Base	Reference	U11151J	-
ID78K0 Integrated Debugger Windows Base	Guide	U11649J	U11649E
ID78K0 Integrated Debugger PC Base	Reference	U11539J	U11539E

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• Documents related to software to be incorporated into the product (user's manual)

Document name		Document No.	
		Japanese	English
78K/0 Series Real-Time OS	Basic	U11537J	U11537E
	Installation	U11536J	U11536E
OS for 78K/0 Series MX78K0	Basic	U12257J	U12257E

• Other documents

Document name	Document No.	
	Japanese	English
NEC IC Package Manual (CD-ROM)	-	C13388E
Semiconductor Device Mounting Technology Manual	C10535J	C10535E
Quality Grades on NEC Semiconductor Device	C11531J	C11531E
NEC Semiconductor Device Reliability/Quality Control System	C10983J	C10983E
Guide to Prevent Damage for Semiconductor Devices by Electrostatic Discharge (ESD)	C11892J	C11892E
Semiconductor Device Quality Control/Reliability Handbook	C12769J	-
Guide for Products Related to Micro-Computer: Other Companies	U11416J	-

Caution The above documents may be revised without notice. Use the latest versions when you design an application system.

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NOTES FOR CMOS DEVICES -

1 PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

Caution This product contains an I²C bus interface circuit.

When using the I²C bus interface, notify its use to NEC when ordering custom code. NEC can guarantee the following only when the customer informs NEC of the use of the interface: Purchase of NEC I²C components conveys a license under the Philips I²C Patent Rights to use these components in an I²C system, provided that the system conforms to the I²C Standard Specification as defined by Philips.

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PC/AT is a trademark of IBM Corporation.

HP9000 series 700 and HP-UX are trademarks of Hewlett-Packard.

SPARCstation is a trademark of SPARC International, Inc.

Solaris and SunOS are trademarks of Sun Microsystems, Inc.

NEWS and NEWS-OS are trademarks of SONY Corporation.



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- · Device availability
- Ordering information
- · Product release schedule
- · Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- Network requirements

In addition, trademarks, registered trademarks, export restrictions, and other legal issues may also vary from country to country.

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Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.

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